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## N-Channel QFET<sup>®</sup> MOSFET

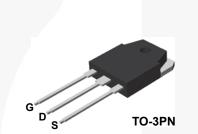
250 V, 62 A, 35 mΩ

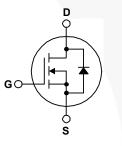
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- + 62 A, 250 V,  $R_{DS(on)}$  = 35 m $\Omega$  (Max.) @ V\_{GS} = 10 V,  $I_{D}$  = 31 A
- Low Gate Charge (Typ. 100 nC)
- Low Crss (Typ. 63.5 pF)
- 100% Avalanche Tested





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQA62N25C	Unit V	
V <sub>DSS</sub>	Drain-Source Voltage	250		
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	62	A	
	- Continuous (T <sub>C</sub> = 100°C)	39	A	
I <sub>DM</sub>	Drain Current - Pulsed (Note 1	) 248	A	
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2	) 2300	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1	) 62	A	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1	(Note 1) 29.8		
dv/dt	Peak Diode Recovery dv/dt (Note 3	) 5.5	V/ns	
PD	Power Dissipation (T <sub>C</sub> = 25°C)	298	W	
	- Derate above 25°C	2.38	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C	

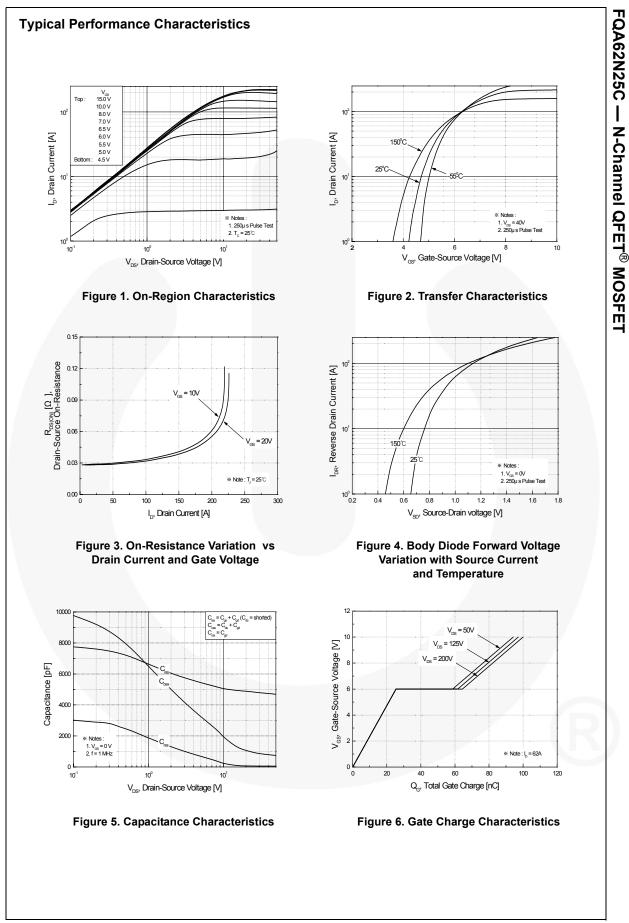
#### **Thermal Characteristics**

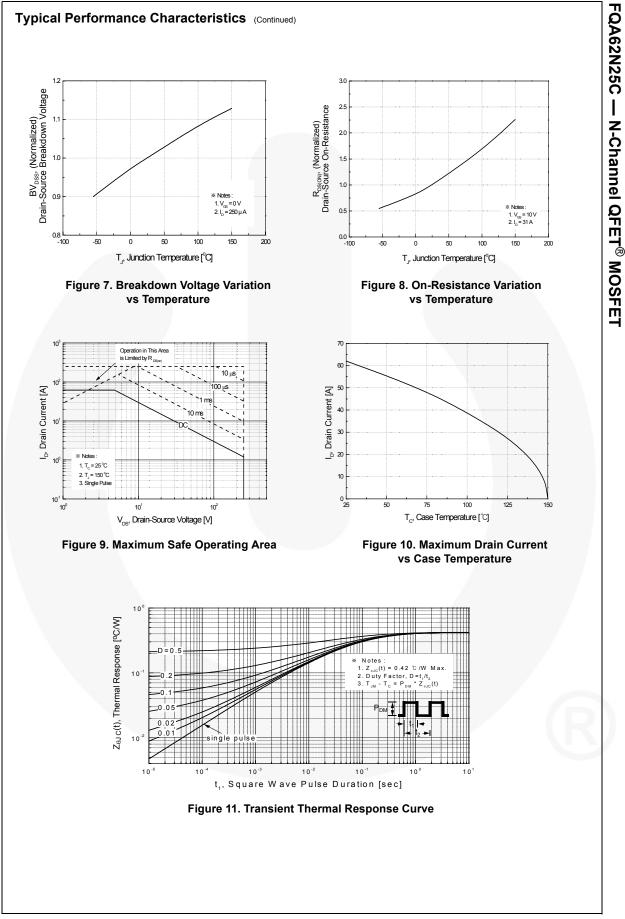
Symbol	Parameter	FQA62N25C	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

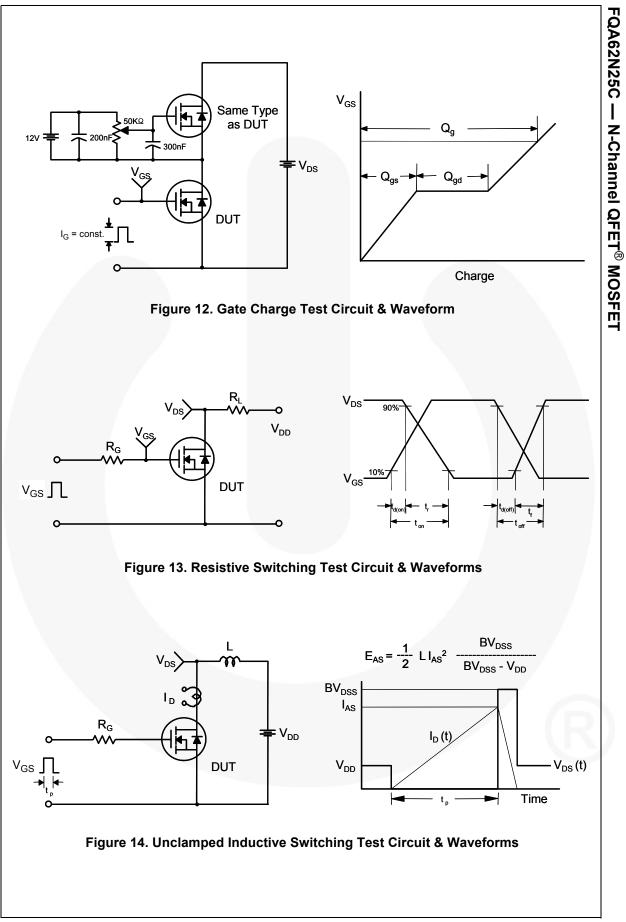
April 2014

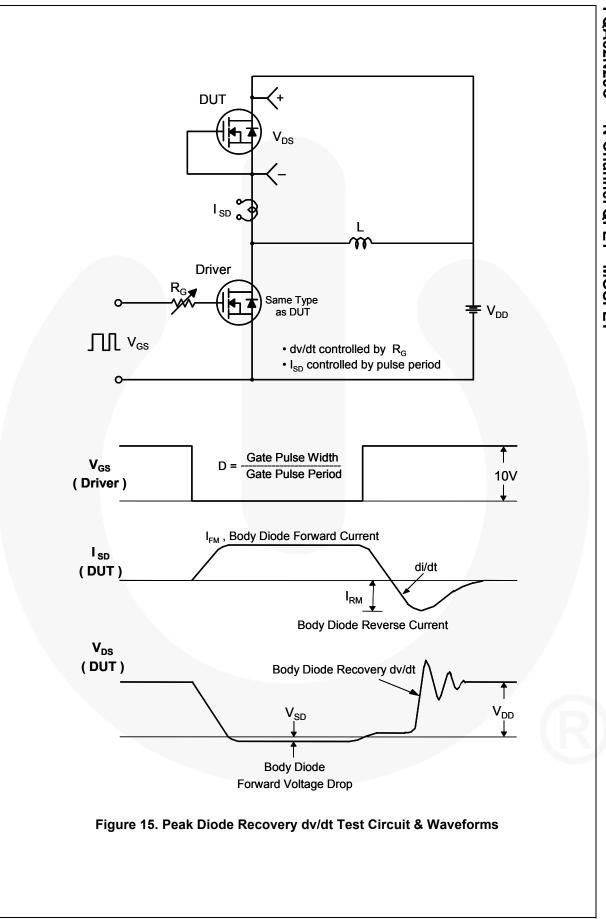
Part Nu	ımber	Top Mark	Pack	age Packing		g Method	Reel S	Size	Tape Width		Quantity
FQA62N25C		C FQA62N25C TO		3PN Tube N/		٩	N/A		30 units		
lootrid	al Ch	orootoriotioo	0								
Symbol		Parameter	Γ <sub>C</sub> = 25°C unl	ess othen	wise noted. Test Con	ditions		Min.	Тур.	Max.	Unit
-		-4:								I	
BV <sub>DSS</sub>	Drain-Se	stics ource Breakdown Vol	ane	Vcs =	= 0 V, I <sub>D</sub> = 25	0 µA		250			V
ABV <sub>DSS</sub>		Breakdown Voltage Temperature									
$\Delta T_{J}$	Coefficient		$I_D = 250 \ \mu A$ , Referenced to $25^{\circ}C$				0.28		V/°C		
DSS	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V					10	μA		
			V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C					100	μA		
GSSF		ody Leakage Current,		$V_{GS}$ = 30 V, $V_{DS}$ = 0 V					100	nA	
GSSR	Gate-Bo	ody Leakage Current,	Reverse	V <sub>GS</sub> =	= -30 V, V <sub>DS</sub>	= 0 V				-100	nA
On Cha	racteris	stics									
/ <sub>GS(th)</sub>	1	reshold Voltage		V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 2	50 µA		2.0		4.0	V
R <sub>DS(on)</sub>	Static Dr On-Resi	rain-Source istance		V <sub>GS</sub> =	= 10 V, I <sub>D</sub> = 31	A			0.029	0.035	Ω
FS	Forward	Transconductance	_	V <sub>DS</sub> =	= 40 V, I <sub>D</sub> = 3	1 A			55		S
viss voss vrss	Input Ca Output 0	acteristics apacitance Capacitance Transfer Capacitanc	e		= 25 V, V <sub>GS</sub> = 0 MHz	: 0 V,			4830 945 63.5	6280 1230 83	pF pF pF
D ita h i		ve et e vietie e									
		Delay Time							75	160	ns
d(on) r		Rise Time	-		= 125 V, I <sub>D</sub> =	62 A,			395	800	ns
d(off)		f Delay Time	-	R <sub>G</sub> =	25 Ω				245	500	ns
f		f Fall Time	-				(Note 4)		335	680	ns
ג <sub>מ</sub>	Total Ga	ate Charge		Vpc =	= 200 V, I <sub>D</sub> =	62 A			100	130	nC
ק ג <sub>gs</sub>		ource Charge			= 10 V	0274,			25.5		nC
ג ג <sup>gd</sup>	Gate-Dr	ain Charge					(Note 4)		39		nC
		Dia da Ohanaatan				- 4!					
s	1	Diode Character								62	A
S SM		m Pulsed Drain-Sour				•				248	A
/ <sub>SD</sub>		ource Diode Forward			= 0 V, I <sub>S</sub> = 62	A				1.5	V
rr		Recovery Time			= 0 V, I <sub>S</sub> = 62				340		ns
ג גער	Reverse	Recovery Charge		00	it = 100 A/μs				4.77		μC
L = 0.96 mH I <sub>SD</sub> ≤ 62 A, c	l, I <sub>AS</sub> = 62 A, di/dt ≤ 300 A/	width limited by maximum ju $V_{DD} = 50 V$ , $R_g = 25 \Omega$ , star $\mu$ s, $V_{D} \le BV_{DSS}$ , starting TJ of operating temperature.	ing T <sub>J</sub> = 25°C								

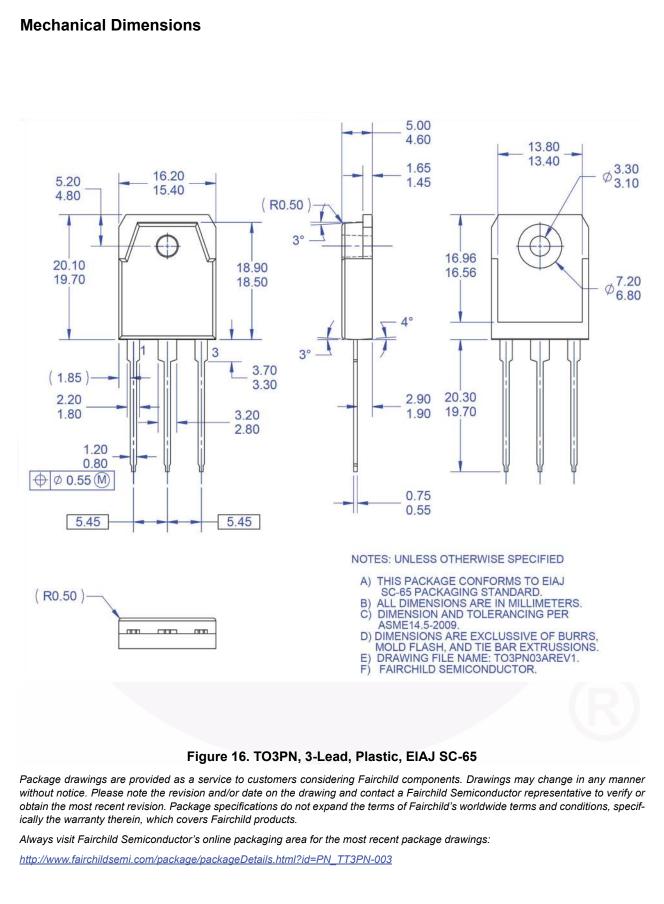
FQA62N25C — N-Channel QFET<sup>®</sup> MOSFET













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